PlasmaTherm 790 Reactive Ion Etcher

Tool Overview

The PlasmaTherm 790 is a parallel plate configuration for etching. The chamber is configured primarily for reactive ion etching (RIE) of semiconductors such as Si, SiC, and GaAs.

Tool Capabilities:

- Sample size up to 8” wafers
- Single bias RF source – 500 watts at 13.56MHZ
- Pressure range: 5mT to 300mT (RIE)
- RIE Gases: SF6, O2, Ar, Cl
- Etch materials: Si, SiC, GaAs, etc